

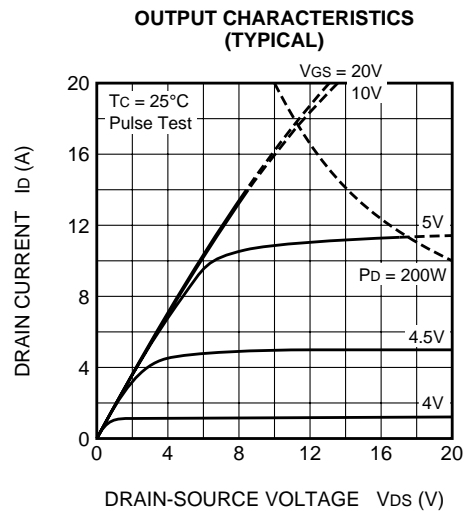
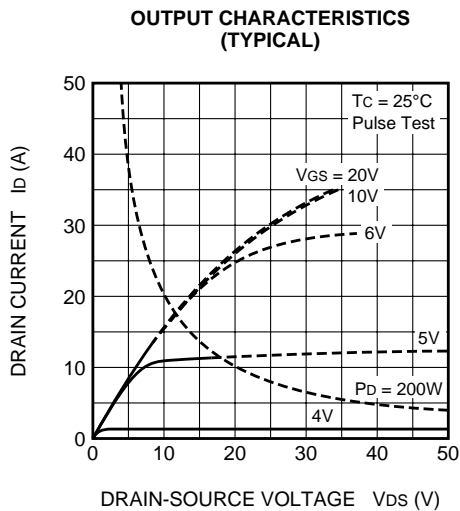
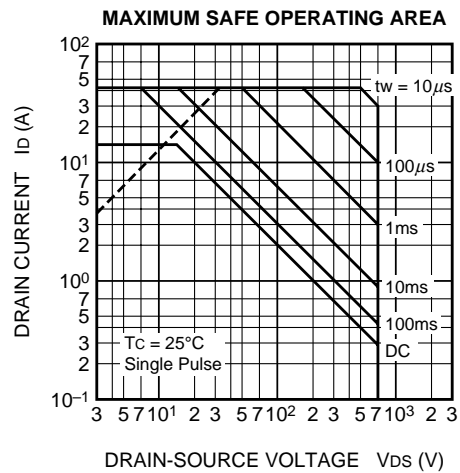
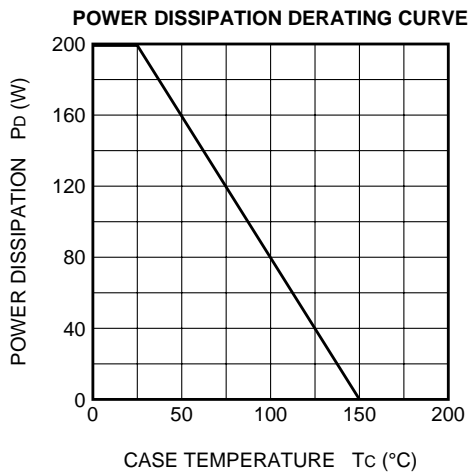
FS14SM-14A

HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

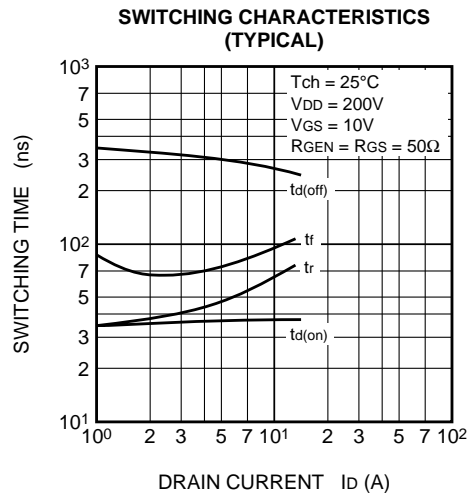
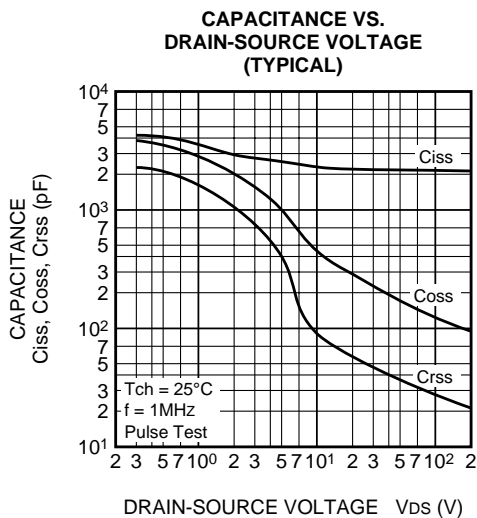
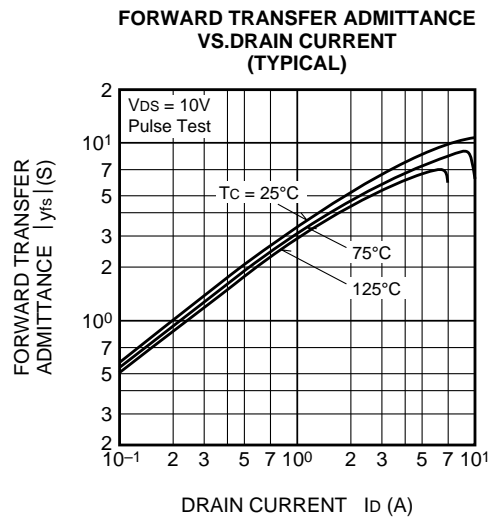
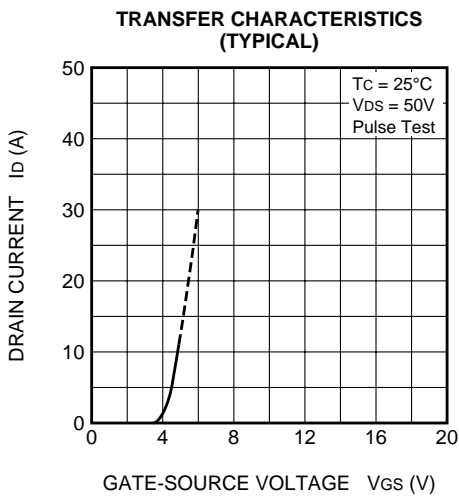
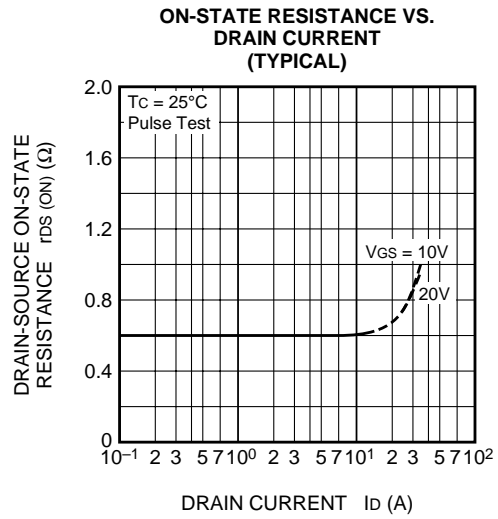
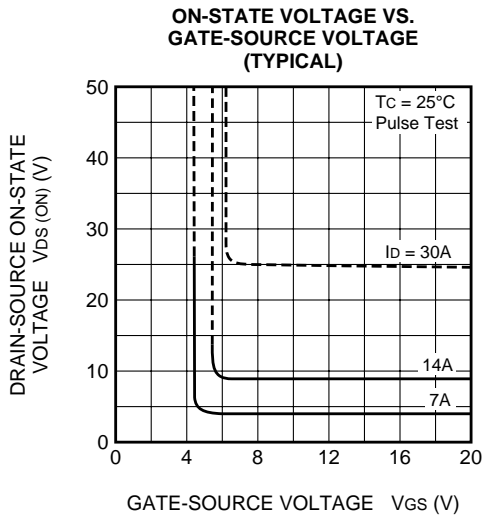
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	700	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _{GS} = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 700V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2	3	4	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 7A, V _{GS} = 10V	—	0.60	0.78	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 7A, V _{GS} = 10V	—	4.20	5.46	V
y _{fs}	Forward transfer admittance	I _D = 7A, V _{DS} = 10V	7.5	12.0	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	2250	—	pF
C _{oss}	Output capacitance		—	265	—	pF
C _{rss}	Reverse transfer capacitance		—	50	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200V, I _D = 7A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	38	—	ns
t _r	Rise time		—	55	—	ns
t _d (off)	Turn-off delay time		—	270	—	ns
t _f	Fall time		—	85	—	ns
V _{SD}	Source-drain voltage		I _S = 7A, V _{GS} = 0V	—	1.0	1.5
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	0.625	°C/W

PERFORMANCE CURVES

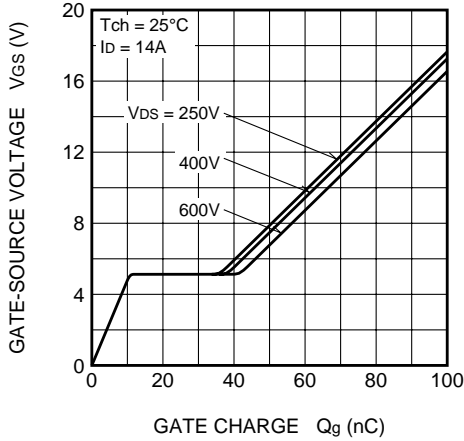


FS14SM-14A

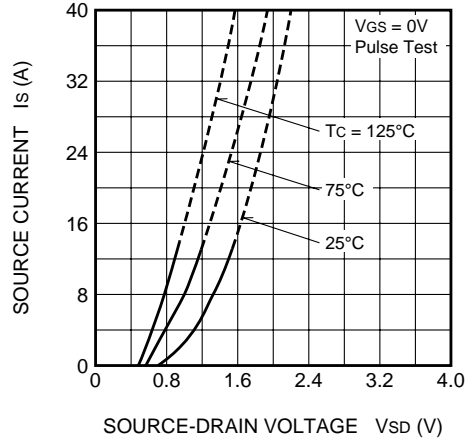
HIGH-SPEED SWITCHING USE



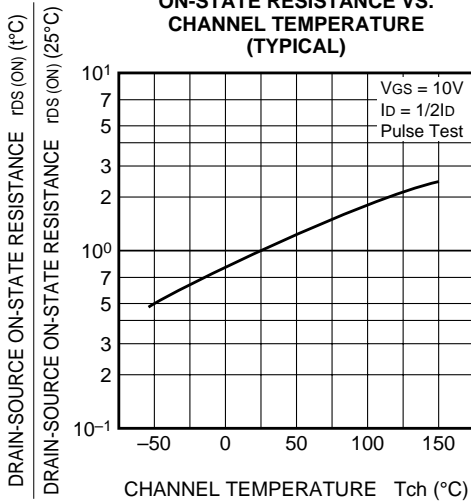
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



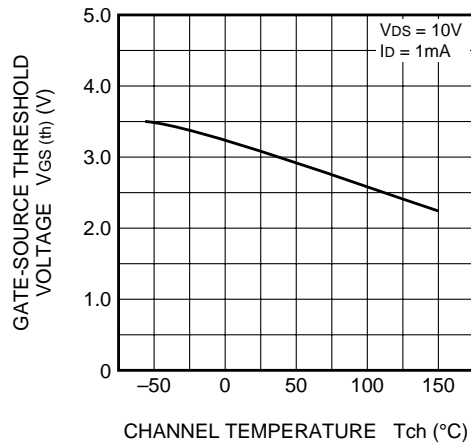
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



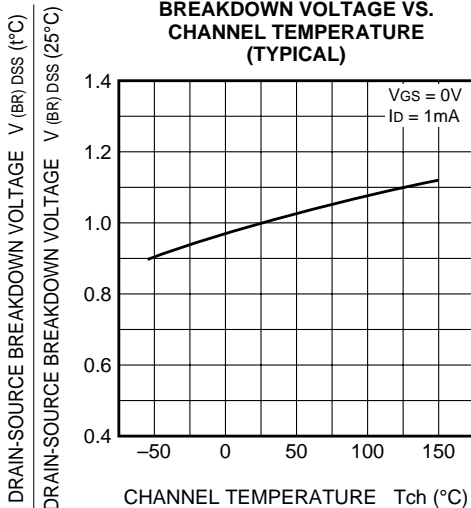
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

